
2N5460, 2N5461, 2N5462

JFET Amplifier P-Channel – Depletion

Features

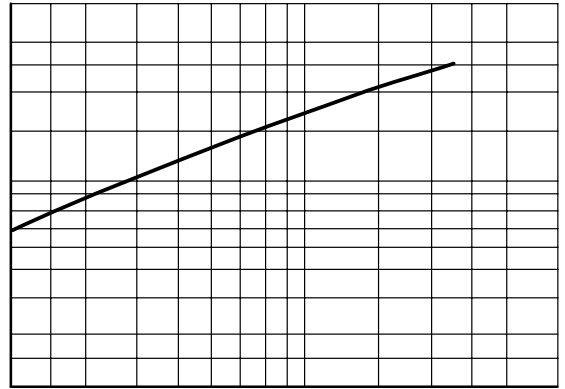
- Pb-Free Packages are Available*

MAXIMUM RATINGS

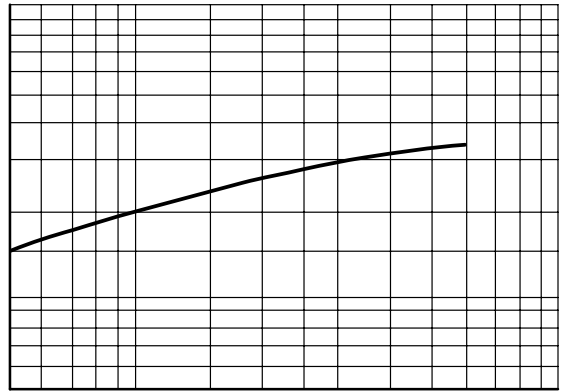
Rating	Symbol	Value	Unit
Drain – Gate Voltage	V_{DG}	40	Vdc
Reverse Gate – Source Voltage	V_{GSR}	40	Vdc
Forward Gate Current	$I_{G(f)}$	10	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	350 2.8	mW mW/ $^\circ\text{C}$
Junction Temperature Range	T_J	-65 to +135	$^\circ\text{C}$
Storage Channel Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

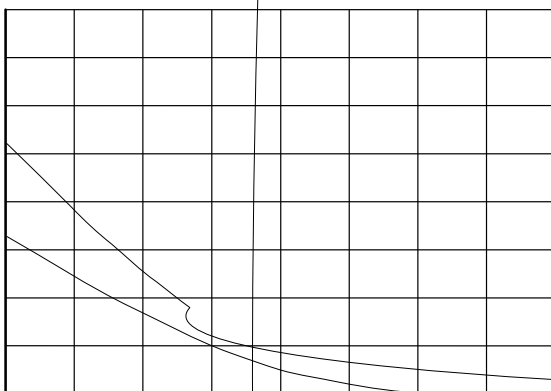
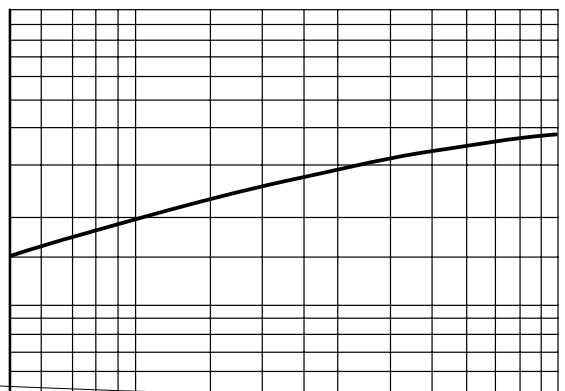
*For additional information on our Pb-Free strategy and soldering details, please



Drain Current (I_D) vs. Gate-Source Voltage (V_{GS})



Drain Current (I_D) vs. Drain-Source Voltage (V_{DS})



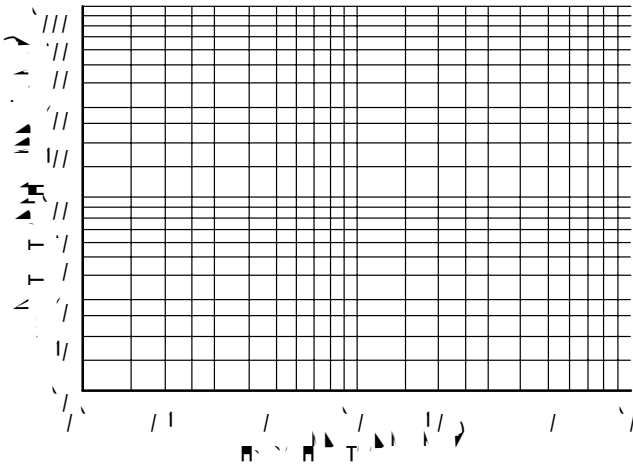


Figure 7. Output Resistance
versus Drain Current

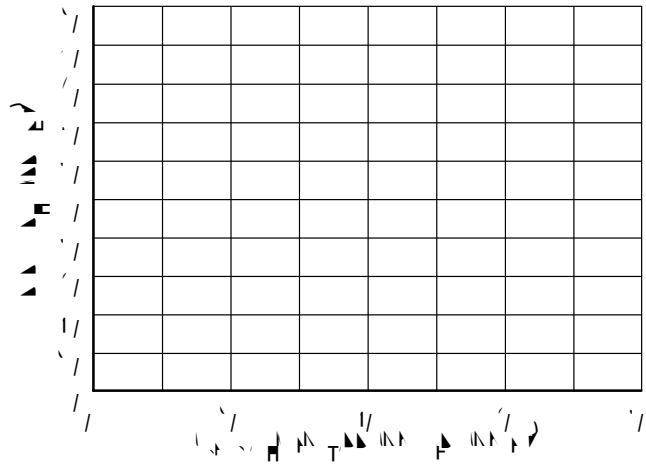


Figure 8. Capacitance versus
Drain-Source Voltage

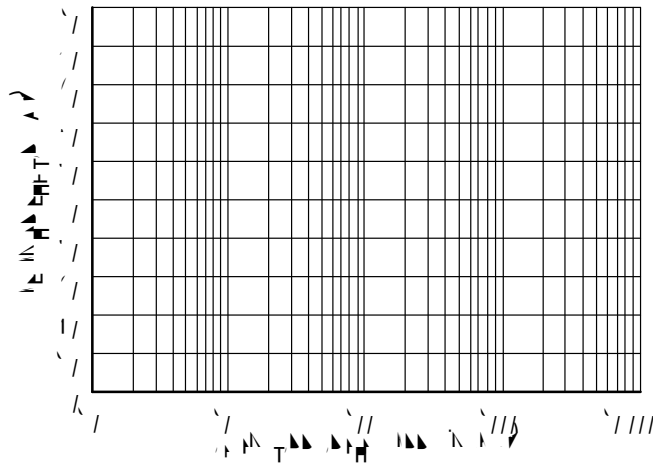


Figure 9. Noise Figure versus
Source Resistance

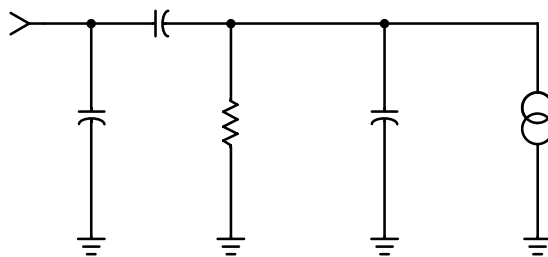


Figure 10. Equivalent Low Frequency Circuit

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PACKAGE DIMENSIONS

TO-92
CASE 29-11
ISSUE AL

